

isc Silicon NPN RF Transistor

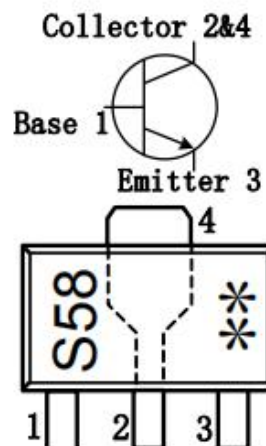
BFU580Q

DESCRIPTION

- Low Noise Figure
 $f_T = 8.5\text{GHz TYP. @ } I_C = 30\text{mA} ; V_{CE} = 8\text{V} ; f = 900\text{MHz}$
- High Gain
 $|S_{21}|^2 = 13\text{dB TYP. @ } I_C = 30\text{mA} ; V_{CE} = 8\text{V} ; f = 900\text{MHz}$
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for use in low noise ,high-gain amplifiers and linear broadband amplifiers.

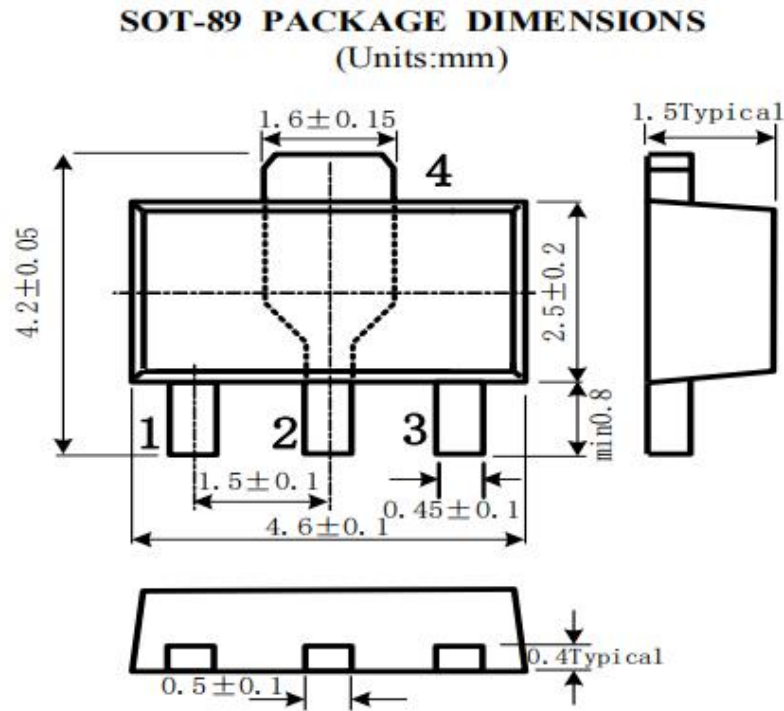


ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	25	V
V_{CEO}	Collector-Emitter Voltage	15	V
V_{EBO}	Emitter-Base Voltage	2.5	V
I_C	Collector Current-Continuous	60	mA
P_C	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	1	W
T_J	Junction Temperature	-40~150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-65~150	$^\circ\text{C}$

isc Silicon NPN RF Transistor**BFU580Q****ELECTRICAL CHARACTERISTICS** $T_c=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = 1\text{mA}$; $I_B = 0$	15			V
I_{CBO}	Collector Cutoff Current	$V_{CB} = 6\text{V}$; $I_E = 0$			0.05	μA
h_{FE}	DC Current Gain	$I_C = 30\text{mA}$; $V_{CE} = 8\text{V}$	60		250	
f_T	Current-Gain—Bandwidth Product	$I_C = 30\text{mA}$; $V_{CE} = 8\text{V}$; $f = 900\text{MHz}$	8	8.5		GHz
C_{re}	Feedback Capacitance	$I_E = 0$; $V_{CB} = 8\text{V}$; $f = 1\text{MHz}$		1.2		pF
C_e	Emitter capacitance	$I_C = I_{C0}$; $V_{EB} = 0.5\text{V}$; $f = 1\text{MHz}$		3.0		pF
C_c	Collector capacitance	$I_E = I_{E0}$; $V_{CB} = 8\text{V}$; $f = 1\text{MHz}$		1.8		pF
$ S_{21} ^2$	Insertion Power Gain	$I_C = 30\text{mA}$; $V_{CE} = 8\text{V}$; $f = 433\text{MHz}$	17	17.5		dB
		$I_C = 30\text{mA}$; $V_{CE} = 8\text{V}$; $f = 900\text{MHz}$	12.5	13		
		$I_C = 30\text{mA}$; $V_{CE} = 8\text{V}$; $f = 1800\text{MHz}$	7.5	8		
G_{UM}	maximum power gain	$I_C = 30\text{mA}$; $V_{CE} = 8\text{V}$; $f = 433\text{MHz}$	18.5	19		dB
		$I_C = 30\text{mA}$; $V_{CE} = 8\text{V}$; $f = 900\text{MHz}$	13.5	14		
		$I_C = 30\text{mA}$; $V_{CE} = 8\text{V}$; $f = 1800\text{MHz}$	8	8.5		

isc Silicon NPN RF Transistor**BFU580Q****PACKAGE SIZE DRAWING**

PIN CONNECTIONS
1.Base 2&4. Collector 3.Emitter

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